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Rohm Semiconductor RRS110N03TB1

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RRS110N03

#### **Transistor**

# 4V Drive Nch MOSFET RRS110N03

#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (SOP8).

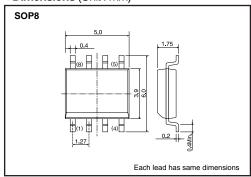
#### Applications

Switching

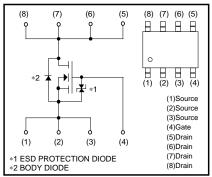
#### Packaging specifications

	Package	Taping
Туре	Code	TB
	Basic ordering unit (pieces)	2500
RRS110N03	0	

#### ●Dimensions (Unit: mm)



#### ●Equivalent circuit



A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

#### ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V <sub>DSS</sub>	30	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	Continuous	ID	±11	Α	
	Pulsed	IDP *1	±44	А	
Source current	Continuous	Is	1.6	А	
(Body diode)	Pulsed	I <sub>SP</sub> *1	44	А	
Total power dissipation		P <sub>D</sub> *2	2.0	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

#### \*2 Mounted on a ceramic board.

#### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	62.5	°C / W

<sup>\*</sup> Mounted on a ceramic board.





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#### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	±10	μΑ	Vgs=±20V, Vps=0V
Drain-source breakdown voltage	V(BR) DSS	30	_	_	V	In=1mA, Vgs=0V
Zero gate voltage drain current	I <sub>DSS</sub>	-	_	1	μΑ	Vps=30V, Vgs=0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	_	2.5	V	VDS=10V, ID=1mA
Static drain-source on-starte resistance		-	9.0	12.6	mΩ	ID=11A, VGS=10V
	RDS (on)	-	11.0	15.4		ID=11A, VGS=4.5V
		-	11.5	16.0		ID=11A, VGS=4V
Forward transfer admittance	Y <sub>fs</sub> *	10	_	_	S	ID=11A, VDS=10V
Input capacitance	Ciss	-	2000	_	pF	V <sub>DS</sub> =10V
Output capacitance	Coss	-	330	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	1	280	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	16	_	ns	I <sub>D</sub> =5.5A, V <sub>DD</sub> ≒15V
Rise time	tr *	-	60	_	ns	V <sub>GS</sub> =10V
Turn-off delay time	t <sub>d (off)</sub> *	-	80	_	ns	R <sub>L</sub> =2.73Ω
Fall time	t <sub>f</sub> *	-	100	-	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	-	22.0	33.0	nC	I <sub>D</sub> =11A, V <sub>DD</sub> ≒15V
Gate-source charge	Q <sub>gs</sub> *	-	5.5	_	nC	V <sub>GS</sub> =5V
Gate-drain charge	Q <sub>gd</sub> *	-	7.5	-	nC	RL=1.36Ω, R <sub>G</sub> =10Ω

<sup>\*</sup>Pulsed

#### ●Body diode characteristics (Source-Drain) (Ta=25°C)

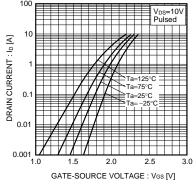
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub> *	_	_	1.2	V	I <sub>S</sub> =11A, V <sub>GS</sub> =0V

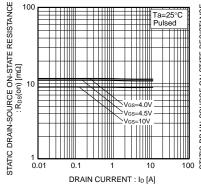
<sup>\*</sup>Pulsed

#### RRS110N03

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#### Electrical characteristic curves





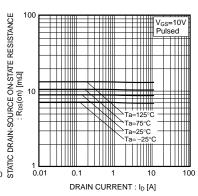
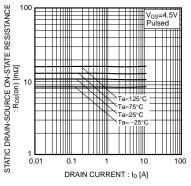
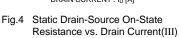


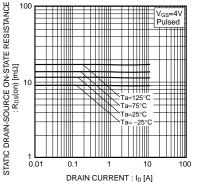
Fig.1 Typical Transfer Characteristics

Fig.2 Static Drain-Source On-State Resistance vs. Drain Current(I)

Fig.3 Static Drain-Source On-State Resistance vs. Drain Current(II)







rig.5 Static Drain-Source On-State Resistance vs. Drain Current(IV)

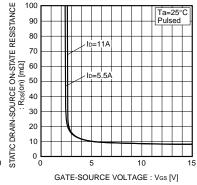


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

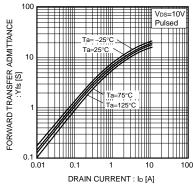


Fig.7 Forward Transfer Admittance vs. Drain Current

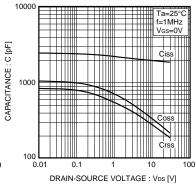


Fig.8 Typical Capacitance vs. Drain-Source Voltage

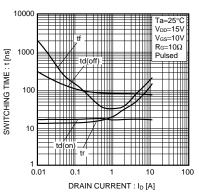


Fig.9 Switching Characteristics

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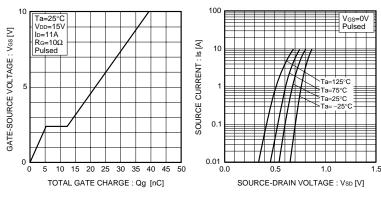


Fig.10 Dynamic Input Characteristics

Fig.11 Source Current vs. Source-Drain Voltage

#### ●Measurement circuit

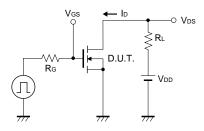


Fig.12 Switching Time Test Circuit

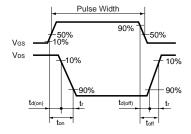


Fig.13 Switching Time Waveforms

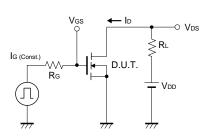


Fig.14 Gate Charge Test Circuit

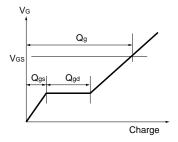


Fig.15 Gate Charge Waveform

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Datasheet of RRS110N03TB1 - MOSFET N-CH 30V 11A 8-SOIC

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#### Appendix

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